ELC-660-23-1

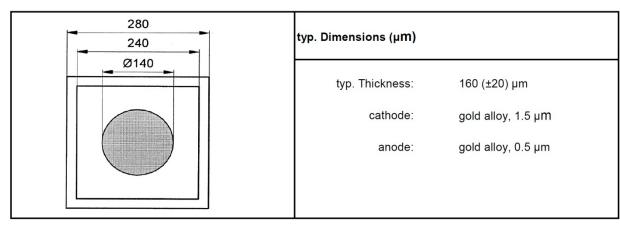
v1 2011

- LED bare chip die
- 660 nm





Radiation	Туре	Electrodes
Red	DDH	N (cathode) up



Optical and Electrical Characteristics

T_{amb}= 25℃, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =20mA	V_{F}		1.8	2.3	V
Reverse voltage	I _R =10μA	V_R	5			V
Radiant power 1	I _F =20mA	Фе	1.5	1.8		mW
Radiant power 2	I _F =20mA	Фе		2.8		mW
Luminous intensity 1	I _F =20mA	I _V	35			mcd
Luminous intensity ²	I _F =20mA	I _V		55		mcd
Peak wavelength	I _F =20mA	λ_{p}	657	660	663	nm
Specifal bandwidth at	I _F =20mA	$\Delta \lambda_{0.5}$		25		nm
Switching time	I _F =20mA	t_r , t_f		80/ 90		ns

¹ Measured on bare chip on TO18 header

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² Measured on epoxy covered chip on TO18 header